



60V, 50A, 8.6mΩ Fast Switching MOSFETs

Features

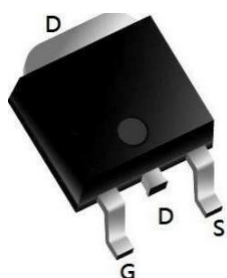
- Super Low Gate Charge
- Advanced high cell density Trench technology
- Excellent CdvV/dt effect decline
- 100% EAS Guaranteed

Applications

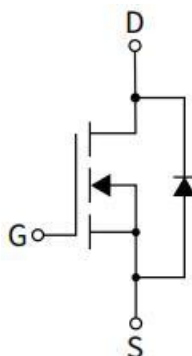
- PWM applications
- Load Switch
- Power management

RoHS

TO252-3L



Equivalent Circuit



Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D @T _C =25°C	50	A
	I _D @T _C =100°C	31	A
Pulsed Drain Current ¹	I _{DM}	200	A
Single Pulse Avalanche Energy ²	EAS	169	mJ
Total Power Dissipation	P _D	57	W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C
Thermal Resistance Junction-ambient	R _{θJA}	-	°C/W
Thermal Resistance Junction-Case	R _{θJC}	2.2	°C/W



Electrical Characteristics($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	-	-	1	μA
		$V_{DS}=60V, V_{GS}=0V, T_J=100^{\circ}\text{C}$	-	-	100	
Gate to Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2.5	V
Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10A$	-	8.6	11	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	10.5	14	
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=30V,$ $f=1.0\text{MHz}$	-	2411	-	pF
Output Capacitance	C_{oss}		-	124	-	
Reverse Transfer Capacitance	C_{rss}		-	116	-	
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=20A,$ $V_{GS}=10V$	-	47.5	-	nC
Gate-Source Charge	Q_{gs}		-	14.5	-	
Gate-Drain("Miller")Charge	Q_{gd}		-	12.7	-	
Turn-on Delay Time	$T_{d(on)}$	$V_{GS}=10V,$ $R_G=1.5\Omega, V_{DD}=30V,$ $I_D=10A$	-	4.3	-	nS
Turn-on Rise Time	t_r		-	6.5	-	
Turn-Off Delay Time	$T_{d(off)}$		-	24	-	
Turn-Off Fall Time	T_f		-	7.6	-	
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.2	V
Continuous Source Current ^{1,5}	I_S	$V_G=V_D=0V, \text{Force Current}$	-	-	50	A
Reverse Recovery Time	T_{rr}	$I_F=10A, di/dt=100A/\mu s$	-	24	-	Ns
Reverse Recovery Charge	Q_{rr}		-	9.3	-	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2O2 copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 3.The EAS data shows Max.'rating . The test condition is $V_{DD}=40V, V_{GS}=10V, L=0.5mH$.
- 4.The power dissipation is limited by 150c junction temperature.
- 5.The data is theoretically the same as I_o and low , in real applications , should be limited by total power dissipation.



Typical Performance Characteristics

Figure 1. Output Characteristics

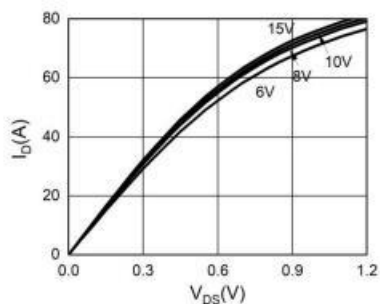


Figure 2. Transfer Characteristics

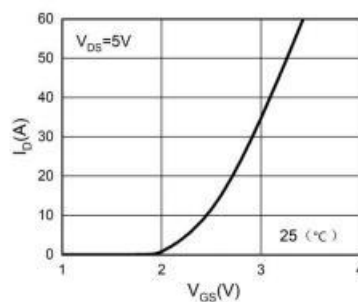


Figure 3. Power Dissipation

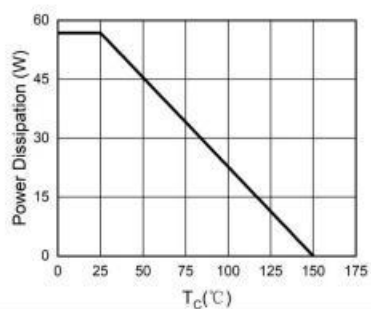


Figure 4. Drain Current

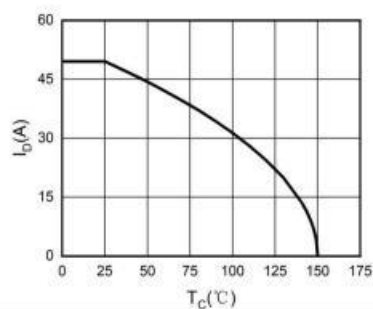


Figure 5. BV_{DSS} vs Junction Temperature

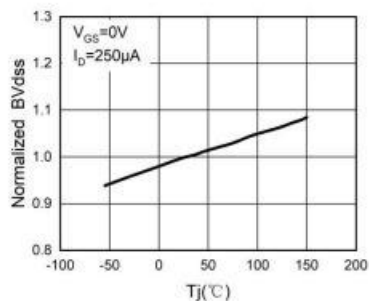


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

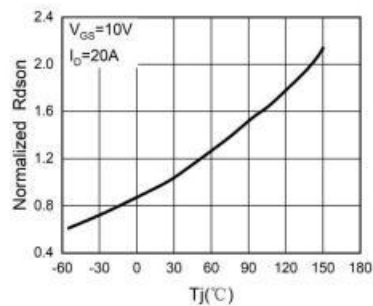




Figure 7. Gate Charge Waveforms

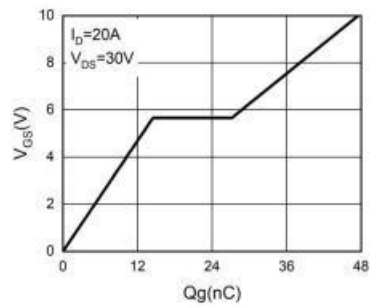


Figure 8. Capacitance

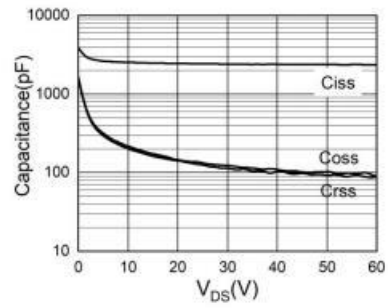


Figure 9. Body-Diode Characteristics

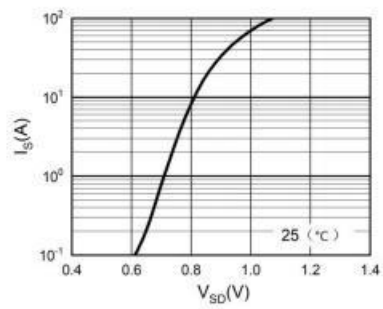
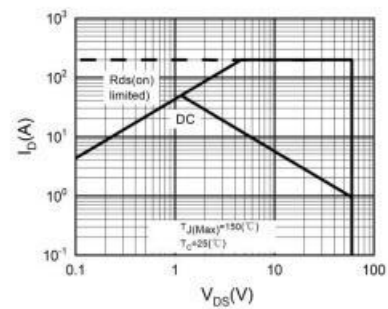
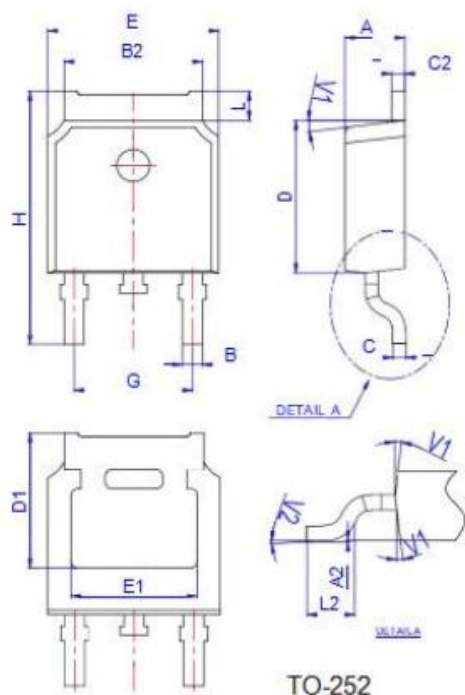


Figure 10. Maximum Safe Operating Area

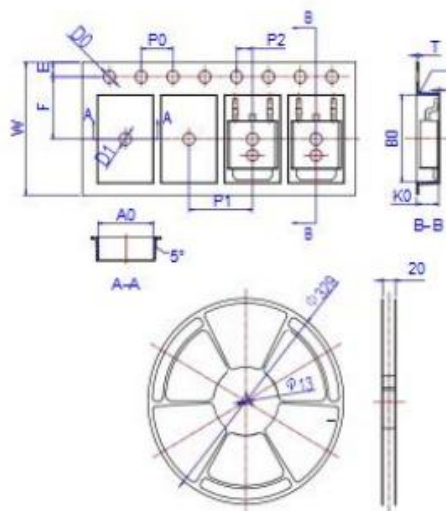




Package Mechanical Data TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.36		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583